

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7507	HBT (heterojunction near bipolar near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:06
L2	174981	FET (field near effect near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:11
L3	4476	InGaP GaInP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:07
L4	22989	etch\$3 near2 stop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:11
L6	134	overheat near protection near circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:08
L7	742	2 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:11
L8	234	4 and 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:11